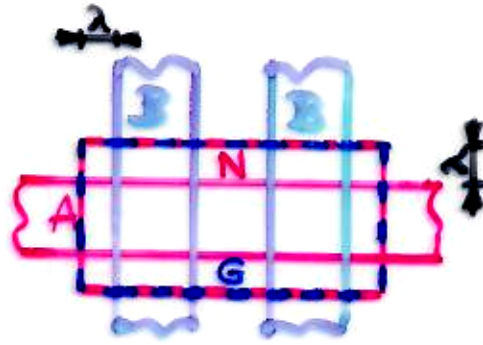


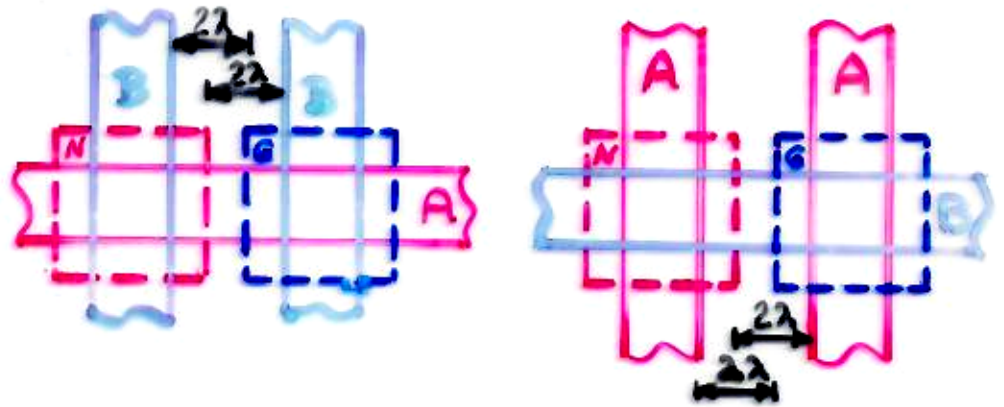
$BN_1, BG_1 = 2\mu$

$AN_1, AG_1 = 2\mu$



$BG_2 = 2\mu$

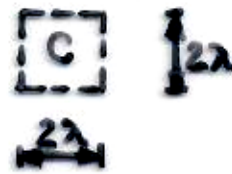
$BN_2 = 3\mu$



$AN_2 = 2\mu$

$AG_2 = 3\mu$

$C_1 = 6\mu$
(C BK)



$F_1 = 5\mu$



$AF_1 = 0\mu$

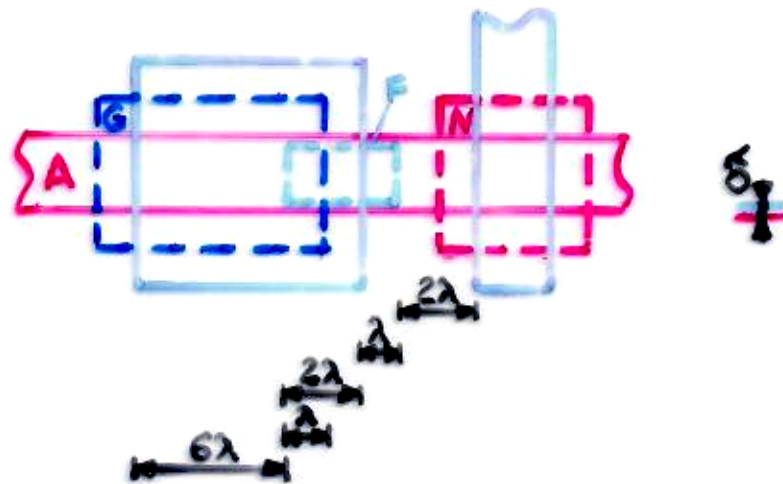
$BF_2 = 3\mu$

$EF_1 = 3\mu$

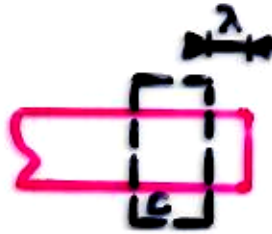
$EF_2 = 5\mu$

$FG_1 = 2\mu$

$BF_3 = 6\mu$

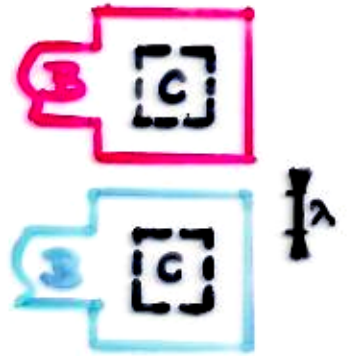


AK1 = 1μ



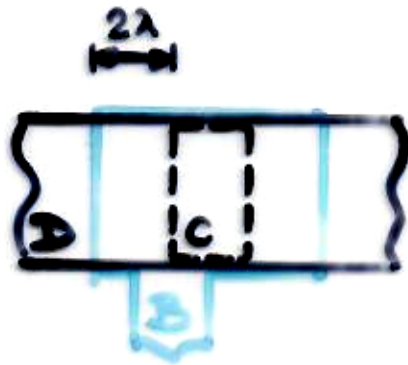
BK1 = 1μ

Ziel: $A \times K = 2 \times 2 \lambda^2$
(nicht prüfbar)



BK1 = 4μ

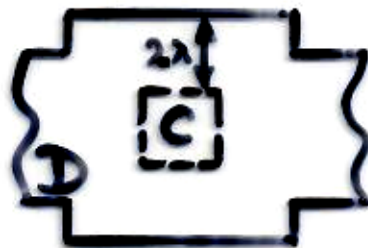
(CD1 = 2μ)



oder:

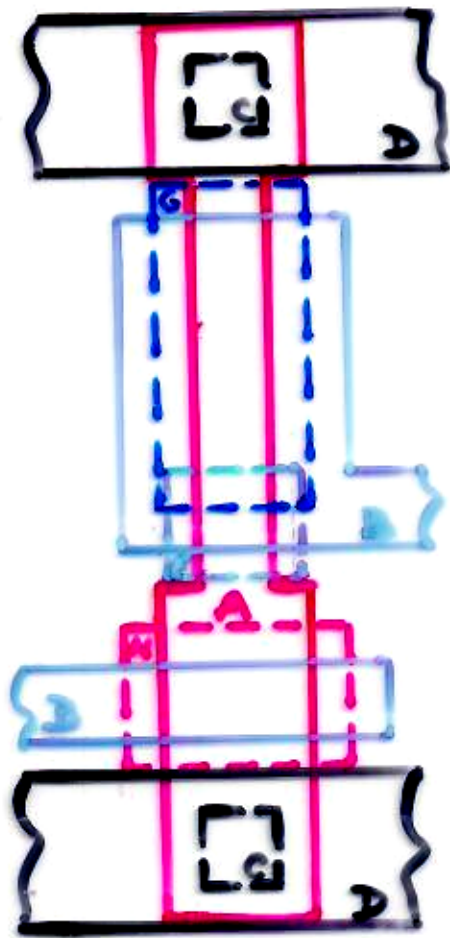
später:

CD1 = 4μ

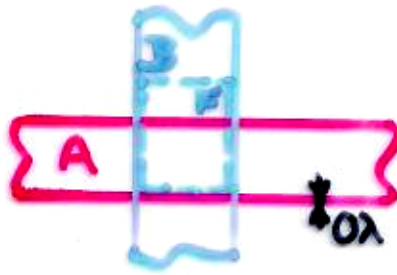


AK2 = 3μ



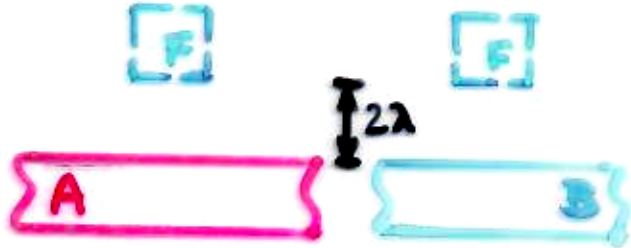


AF1 = 20μ

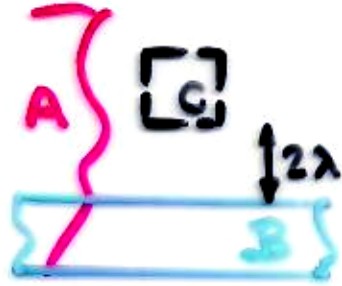


Achtung!
 A-Gebiet wird durch
 B elektrisch unter-
 brochen! erhöhter
 Widerstand.

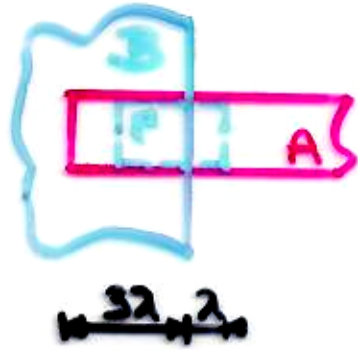
AF2 = 3μ
 BF2 = 3μ



BK2 = 3μ



BF1 = 2μ
 AB4 = 6μ



Verhinderung eines
 parasitären Transistors
 im A-Gebiet: 3F1

Bondinset:
 DE1 = 12μ

